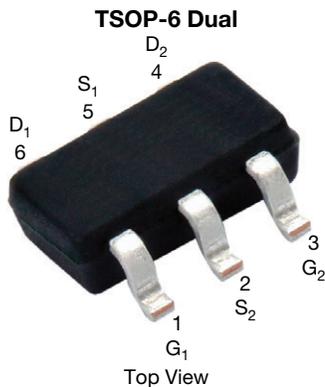


## Automotive N- and P-Channel 20 V (D-S) MOSFET



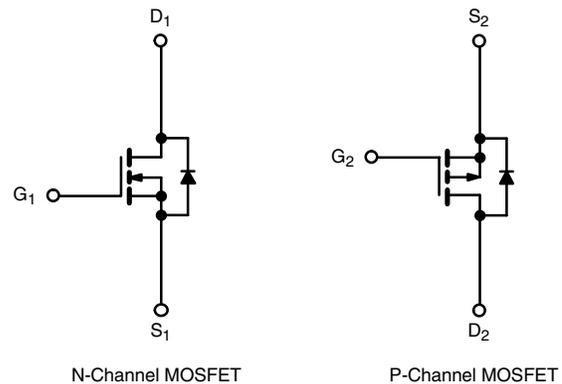
Marking Code: 9U

PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
$V_{DS}$ (V)	20	-20
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = \pm 4.5$ V	0.077	0.166
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = \pm 2.5$ V	0.120	0.318
$I_D$ (A)	3.57	-2.5
Configuration	N- and p-pair	

### FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE GRADE


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**


ORDERING INFORMATION	
Package	TSOP-6 Dual
Lead (Pb)-free and halogen-free	SQ3585CEV (for detailed order number please see <a href="http://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-source voltage	$V_{DS}$	20	-20	V
Gate-source voltage	$V_{GS}$	$\pm 12$	$\pm 12$	
Continuous drain current	$I_D$	$T_C = 25$ °C	3.57	A
		$T_C = 125$ °C	2	
Pulsed drain current	$I_{DM}$	12	-10	
Continuous source current (diode conduction)	$I_S$	2.1	-2.1	
Maximum power dissipation	$P_D$	$T_C = 25$ °C	1.67	W
		$T_C = 125$ °C	0.56	
Unclamped inductive surge UIS	$I_{AV}$	3.3	3	A
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175		°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
		MAX.	MAX.	
Maximum junction-to-ambient <sup>a</sup>	Steady state	$R_{thJA}$	150	°C/W
Maximum junction-to-foot (drain)	Steady state	$R_{thJF}$	90	

#### Note

a. Surface mounted on 1" x 1" FR4 board



<b>SPECIFICATIONS</b> ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
<b>Static</b>								
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		N-Ch	0.6	-	1.5	V
		$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		P-Ch	-0.6	-	-1.5	
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		N-Ch	-	-	$\pm 100$	nA
				P-Ch	-	-	$\pm 100$	
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0 \text{ V}$	$V_{DS} = 20 \text{ V}$	N-Ch	-	-	1	$\mu\text{A}$
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}$	P-Ch	-	-	-1	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 20 \text{ V}, T_J = 55^\circ\text{C}$	N-Ch	-	-	5	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}, T_J = 55^\circ\text{C}$	P-Ch	-	-	-5	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	N-Ch	5	-	-	A
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} \leq -5 \text{ V}$	P-Ch	-5	-	-	
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5 \text{ V}$	$I_D = 1 \text{ A}$	N-Ch	-	0.049	0.077	$\Omega$
		$V_{GS} = -4.5 \text{ V}$	$I_D = -1 \text{ A}$	P-Ch	-	0.140	0.166	
		$V_{GS} = 2.5 \text{ V}$	$I_D = 1 \text{ A}$	N-Ch	-	0.066	0.120	
		$V_{GS} = -2.5 \text{ V}$	$I_D = -1 \text{ A}$	P-Ch	-	0.265	0.318	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 5 \text{ V}, I_D = 1 \text{ A}$		N-Ch	-	7	-	S
		$V_{DS} = -5 \text{ V}, I_D = -1 \text{ A}$		P-Ch	-	3	-	
Diode forward voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.05 \text{ A}, V_{GS} = 0 \text{ V}$		N-Ch	-	0.80	1.10	V
		$I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$		P-Ch	-	-0.83	-1.10	
<b>Dynamic <sup>b</sup></b>								
Total gate charge	$Q_g$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	2.0	3.0	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	3.0	5.0	
Gate-source charge	$Q_{gs}$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	1.0	-	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	1.0	-	
Gate-drain charge	$Q_{gd}$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	1.0	-	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	1.0	-	
Gate resistance	$R_g$	$f = 1 \text{ MHz}$		N-Ch	3.4	-	9.1	$\Omega$
				P-Ch	3.4	-	9.1	
Turn-on delay time	$t_{d(on)}$	N-Channel $V_{DD} = 10 \text{ V}, R_L = 10 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		N-Ch	-	11	17	ns
Rise time	$t_r$			P-Ch	-	9	14	
				N-Ch	-	15	23	
Turn-off delay time	$t_{d(off)}$			P-Ch	-	18	27	
		P-Channel $V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		N-Ch	-	19	29	
Fall time	$t_f$			P-Ch	-	14	21	ns
				N-Ch	-	8	12	
				P-Ch	-	5	9	

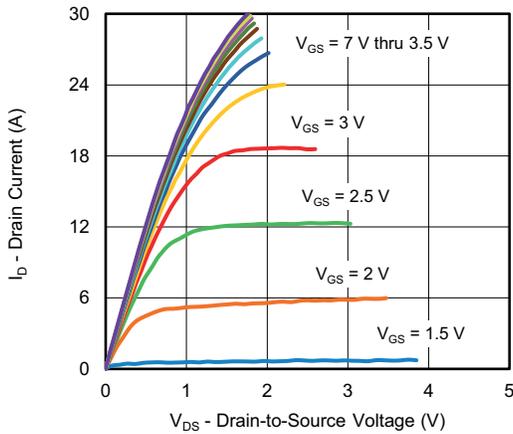
**Notes**

- a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2 \%$
- b. Guaranteed by design, not subject to production testing

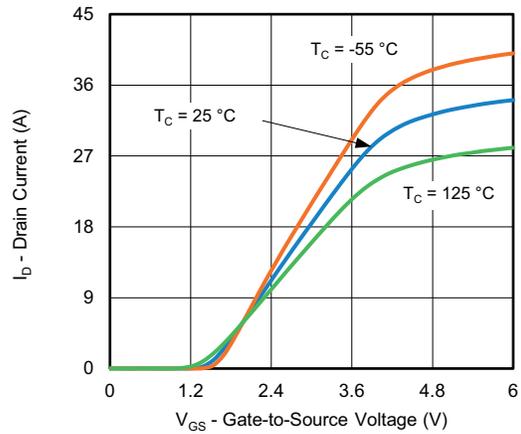
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



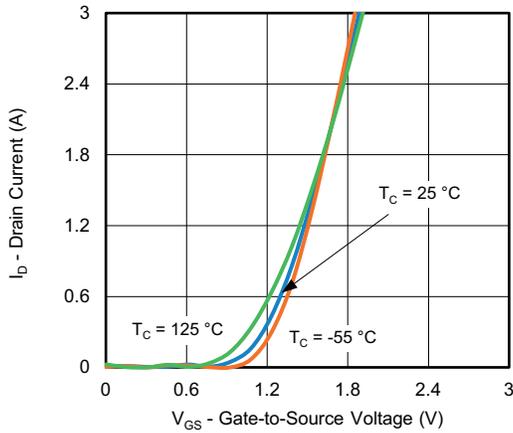
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



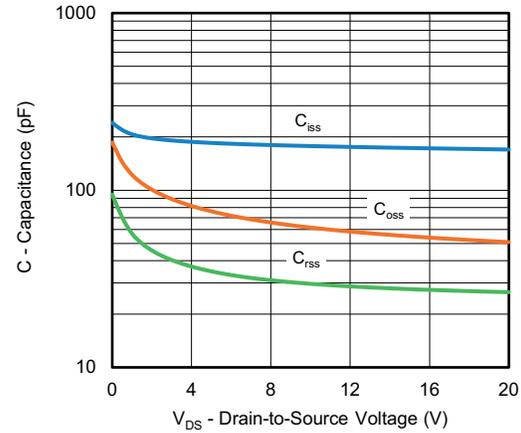
Output Characteristics



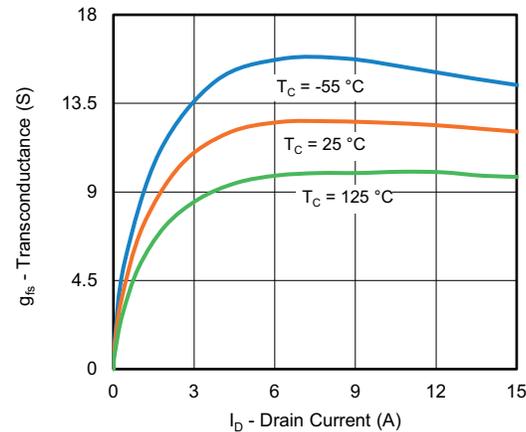
Transfer Characteristics



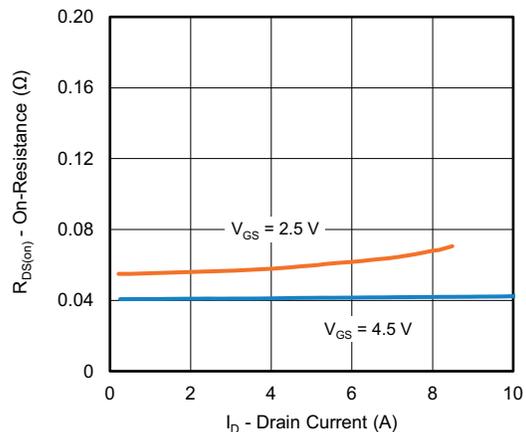
Transfer Characteristics



Capacitance

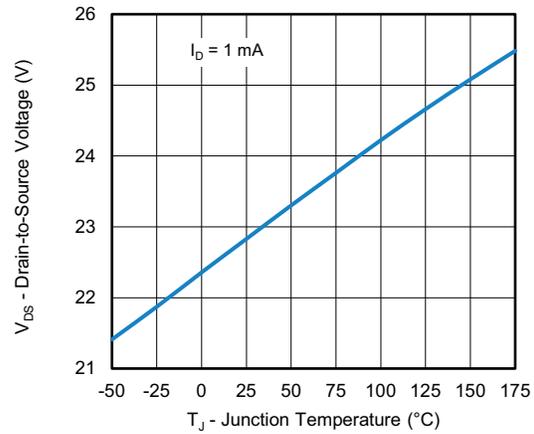
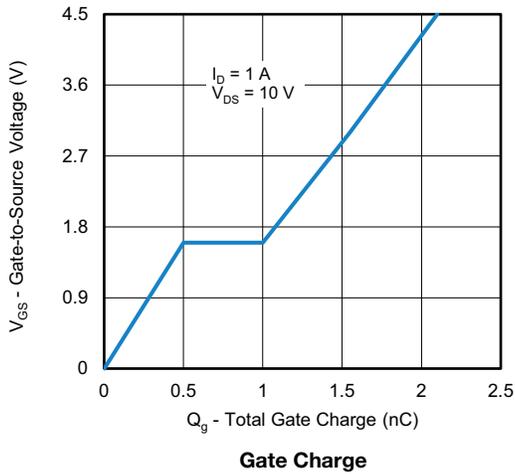


Transconductance

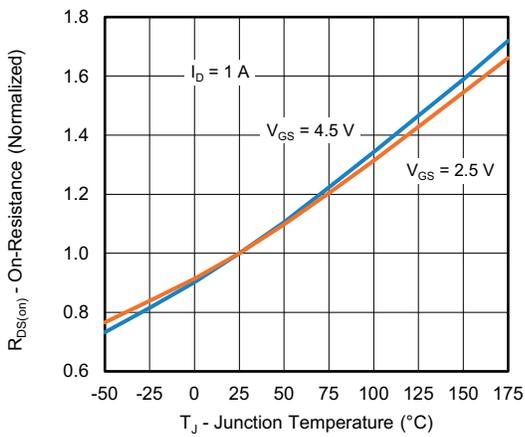


On-Resistance vs. Drain Current

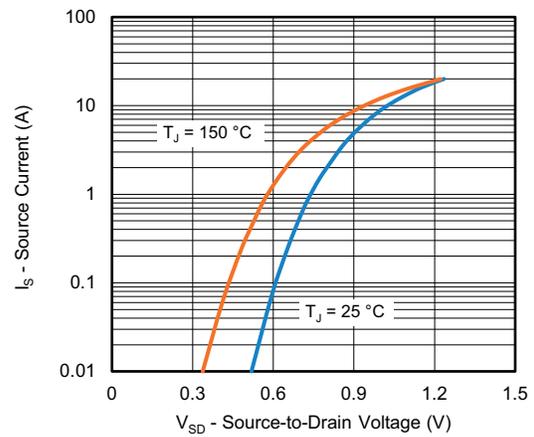
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C unless otherwise noted)



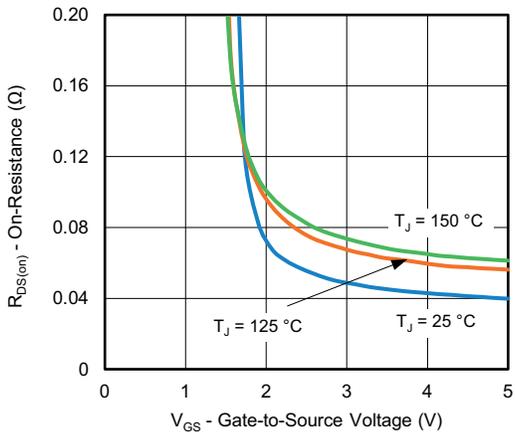
**Drain Source Breakdown vs. Junction Temperature**



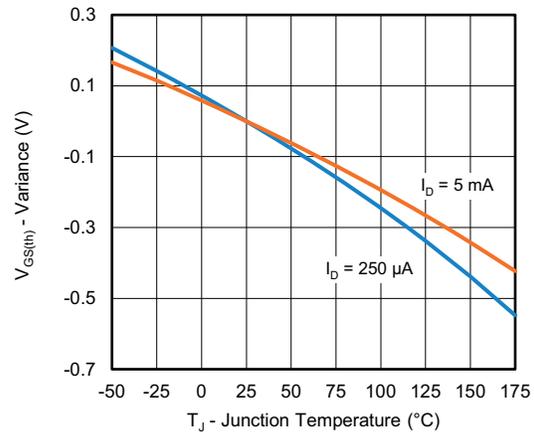
**On-Resistance vs. Junction Temperature**



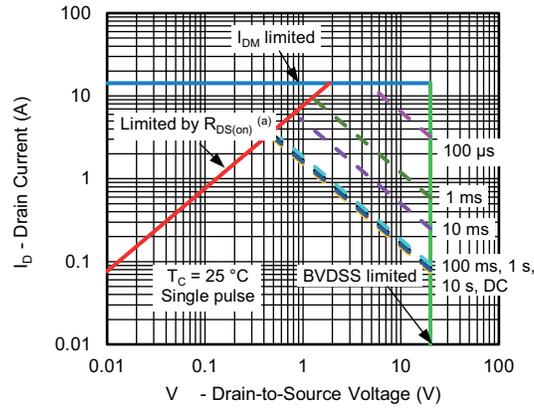
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



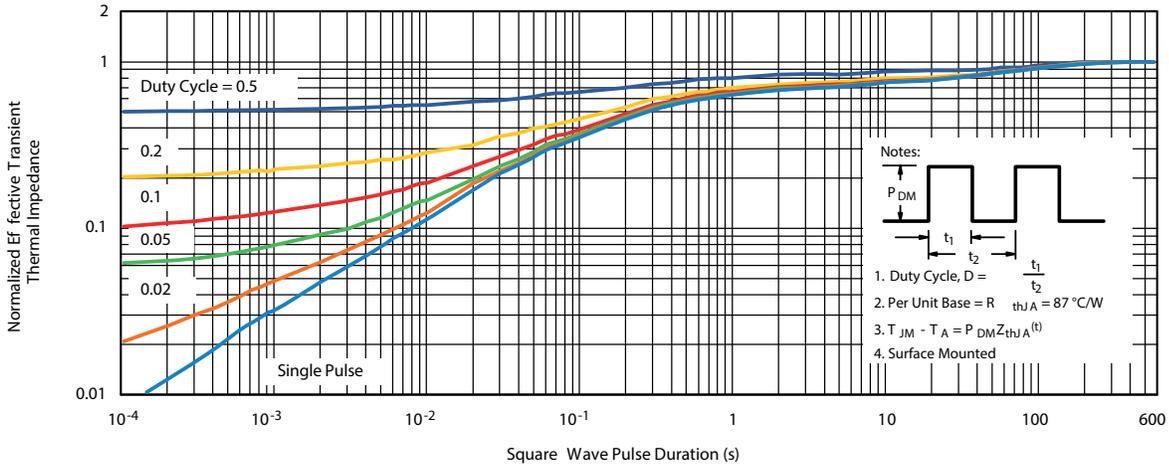
Safe Operating Area

**Note**

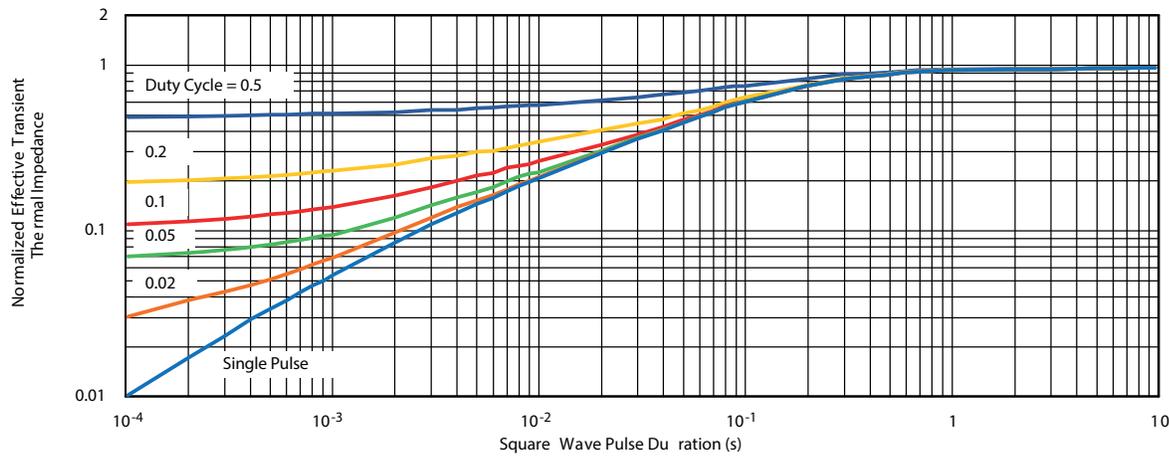
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C unless otherwise noted)



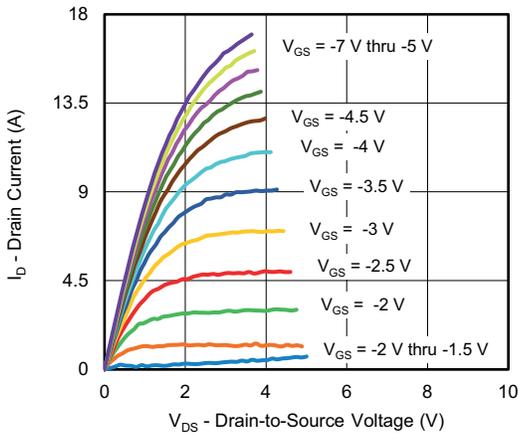
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



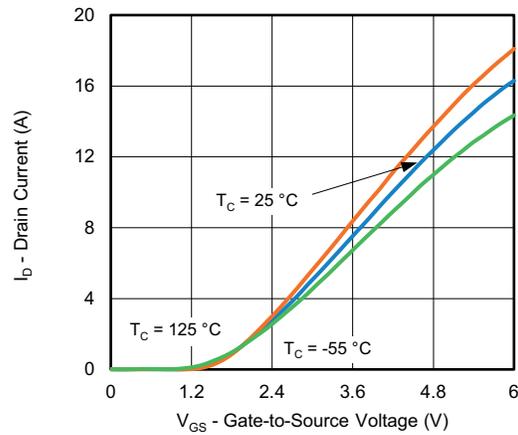
**Normalized Thermal Transient Impedance, Junction-to-Foot**



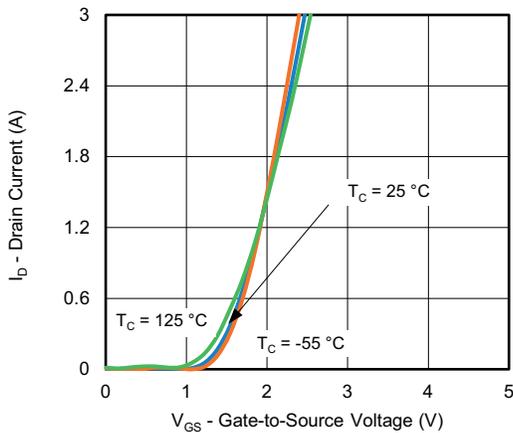
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C unless otherwise noted)



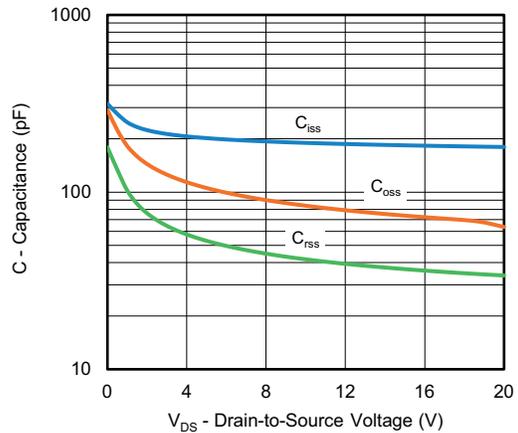
**Output Characteristics**



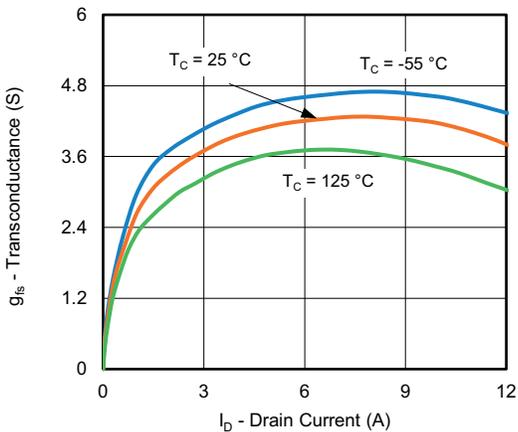
**Transfer Characteristics**



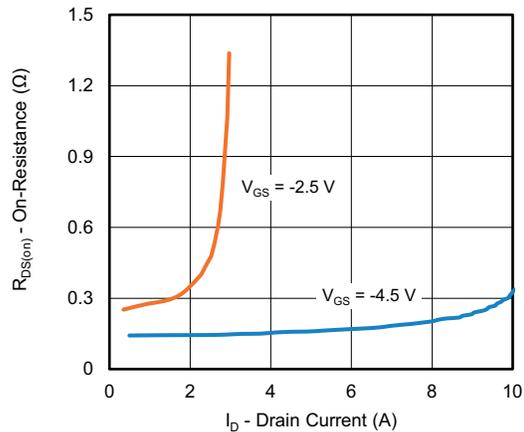
**Transfer Characteristics**



**Capacitance**

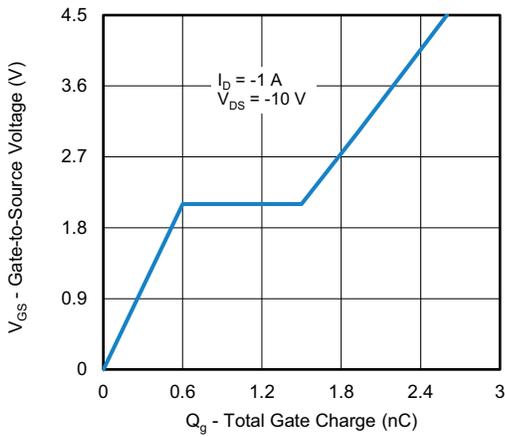


**Transconductance**

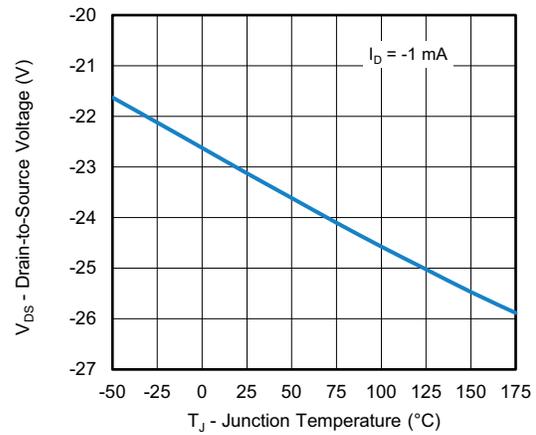


**On-Resistance vs. Drain Current**

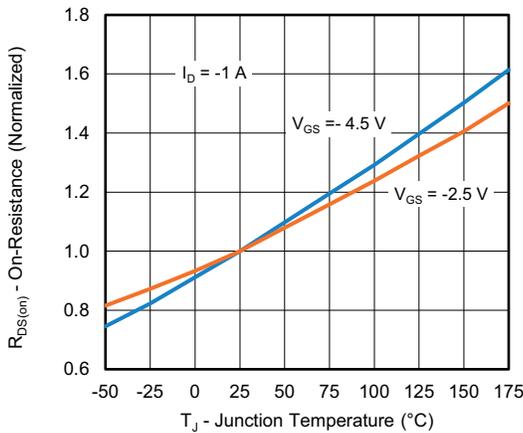
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C unless otherwise noted)



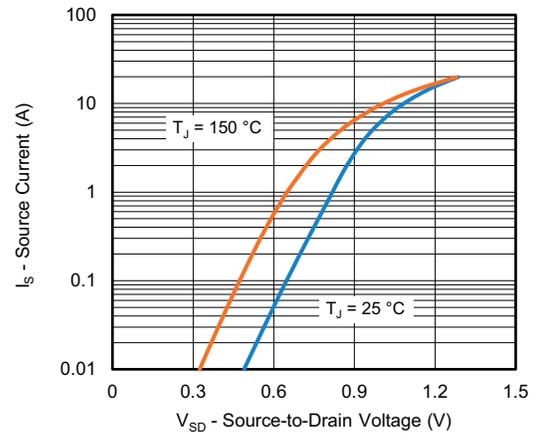
**Gate Charge**



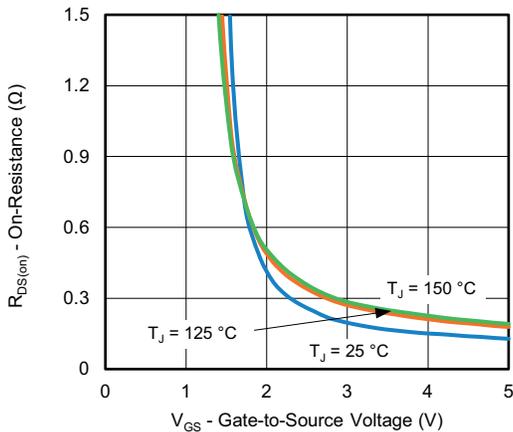
**Drain Source Breakdown vs. Junction Temperature**



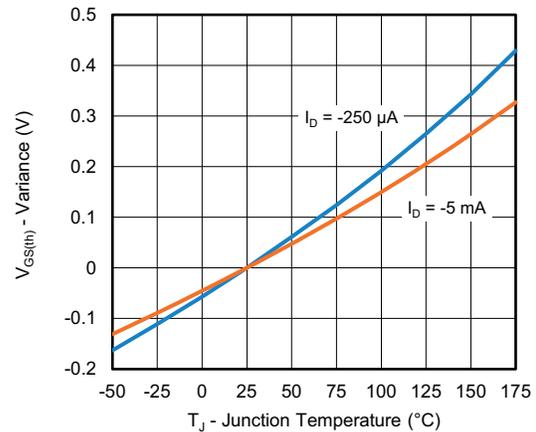
**On-Resistance vs. Junction Temperature**



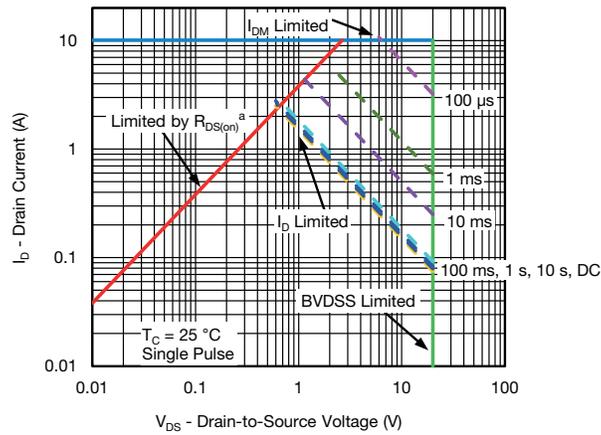
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



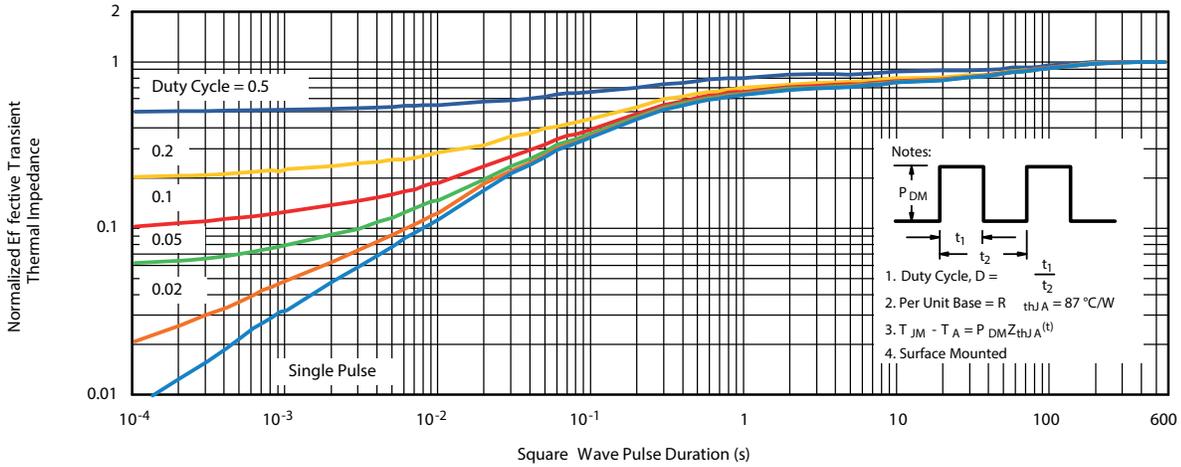
Safe Operating Area

**Note**

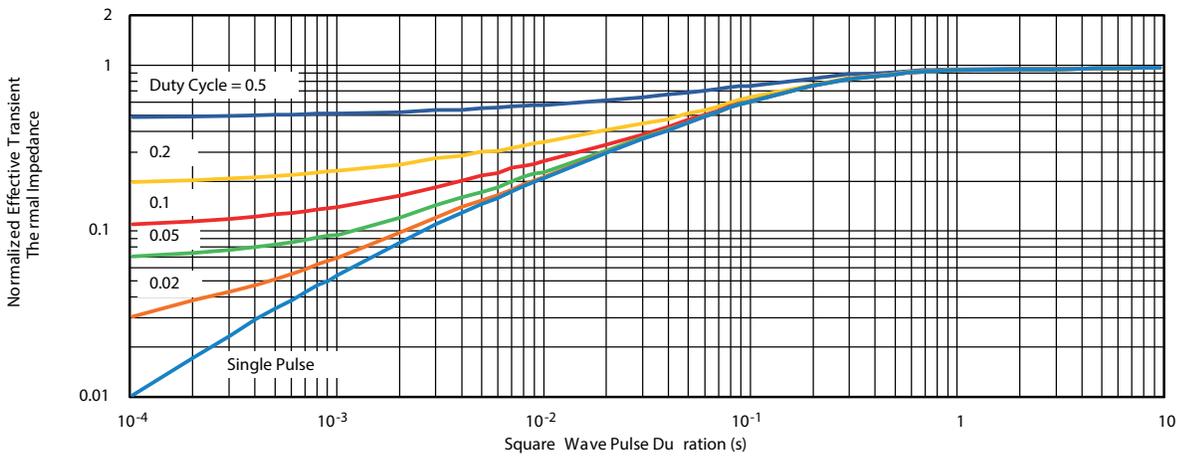
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



P-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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